CLAIMS

1. An imprinting mold comprising:

a flattening layer provided on a substrate, having a layer made of a flattening agent; and

a layer having a fine pattern on the flattening layer~~.~~, wherein

polysilazane is contained in the flattening layer.

2. The imprinting mold according to claim 1, wherein the substrate is a cylindrical substrate made of stainless steel, and the flattening agent is polysilazane.

3. The imprinting mold according to claim 1 or 2, wherein the layer having the fine pattern is a fine pattern forming layer, the fine pattern forming layer including a chromium oxide layer wherein thickness of the chromium oxide layer is larger than 100nm and thickness of a whole body of the fine patter forming layer is larger than 100nm and 1μm or less.

4. The imprinting mold according to claim 1 or 2, wherein the layer having the fine pattern is a fine pattern forming layer, the fine pattern forming layer including a chromium nitride layer, wherein thickness of the chromium nitride layer is 20nm or more and thickness of a whole body of the fine pattern forming

layer is 20nm or more and 1μm or less.

5. The imprinting mold according to claim 1 or 2, wherein the layer having the fine pattern is a fine pattern forming layer, the fine pattern forming layer including a chromium oxide layer and a chromium nitride layer, wherein thickness of the chromium nitride layer is 20nm or more and thickness of a whole body of the fine pattern forming layer is 20nm or more and 1μm or less.

6. The imprinting mold according to claim 1 or 2, wherein the layer having the fine pattern is a fine pattern forming layer, the fine pattern forming layer including an amorphous carbon layer, wherein thickness of the amorphous carbon layer is larger than 50nm and thickness of the fine pattern forming layer is larger than 50nm and 1μm or less.

7. A method of manufacturing an imprinting mold, comprising

flattening a surface of a substrate by coating the substrate with a flattening agent~~.~~, wherein

the flattening agent contains polysilazane.

8. The method of manufacturing the imprinting mold according to claim 7, wherein

the substrate is a cylindrical substrate made of

12. The method according to claim 9, wherein the fine pattern forming layer includes a chromium oxide layer and a chromium nitride layer, and thickness of the chromium nitride layer is 20nm or more, and thickness of a whole body of the fine pattern forming layer is 20nm or more and 1μm or less.

13. The method according to claim 9, wherein the fine pattern forming layer includes an amorphous carbon layer, and thickness of the amorphous carbon layer is larger than 50nm and thickness of the fine pattern forming layer is larger than 50nm and 1μm or less.

14. The method according to claim 9, wherein blue laser drawing is carried out in the drawing process.

15. An imprinting mold substrate comprising:

a flattening layer provided on a substrate, having a layer made of a flattening agent containing polysilazane;

a fine pattern forming layer on the flattening layer; and

a resist layer for forming a fine pattern on the fine pattern forming layer.

16. The imprinting mold substrate according to claim 15, wherein the fine pattern forming layer includes

any of a chromium oxide layer, a chromium nitride layer and an amorphous carbon layer.

17. The imprinting mold substrate according to claim 15, wherein the fine pattern forming layer includes a chromium oxide layer, thickness of the chromium oxide layer is larger than 100nm and thickness of a whole body of the fine pattern forming layer is larger than 100nm and 1μm or less.

18. The imprinting mold substrate according to claim 15, wherein the fine pattern forming layer includes a chromium nitride layer, and thickness of the chromium nitride layer is 20nm or more, and thickness of a whole body of the fine pattern forming layer is 20nm or more and 1μm or less.

19. The imprinting mold substrate according to claim 15, wherein the fine pattern forming layer includes a chromium oxide layer and a chromium nitride layer, and thickness of the chromium nitride layer is 20nm or more, and thickness of a whole body of the fine pattern forming layer is 20nm or more and 1μm or less.

20. The imprinting mold substrate according to claim 15, wherein the fine pattern forming layer includes an amorphous carbon layer, and thickness of the amorphous

carbon layer is larger than 50nm and thickness of the fine pattern forming layer is larger than 50nm and 1μm or less.